

isc Silicon NPN Power Transistor

2SD5703

DESCRIPTION

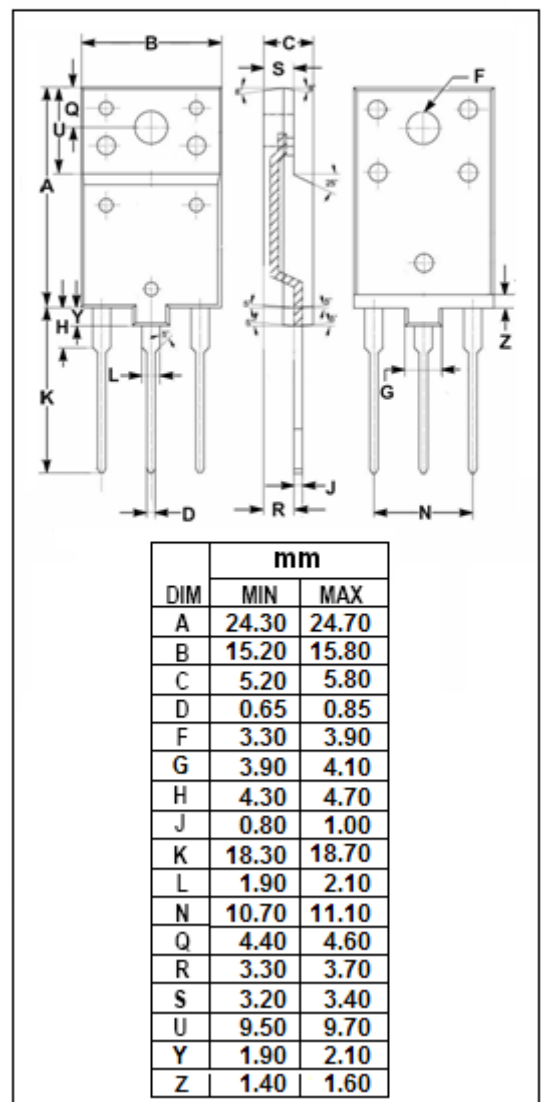
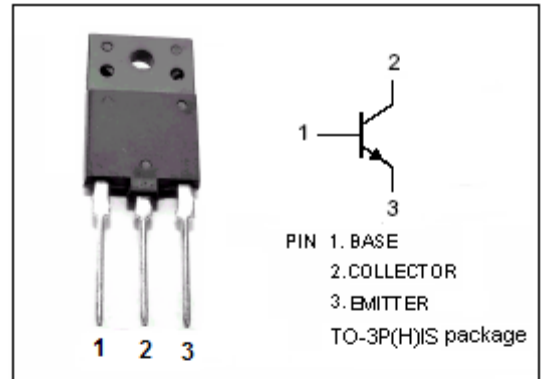
- High Breakdown Voltage-
: $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- Low Saturation Voltage

APPLICATIONS

- Designed for color TV horizontal output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	10	A
I_C	Collector Current- Pulse	30	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	70	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SD5703****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1400V; V _{BE} = 0			1	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μ A
I _{CBO}	Collector Cutoff Current	V _{EB} = 4V; I _C = 0			1	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	15		40	
h _{FE-2}	DC Current Gain	I _C = 8A; V _{CE} = 5V	5.3		7.3	
t _f	Fall Time	I _C = 6A, I _{B1} = 1.2A; I _{B2} = -2.4A; V _{CC} = 200V; R _L = 33.3 Ω			0.3	μ s